2SD667(A)T

Rev.A May.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

/ Features

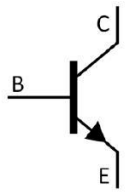
2SB647(A)T

Complementary pair with 2SB647(A)T.

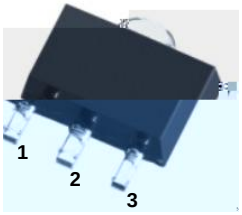
/ Applications

Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

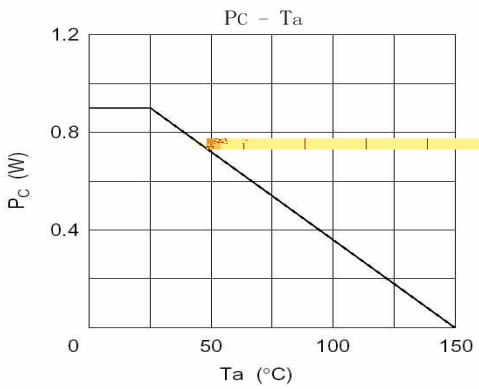
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320
Marking	H67B **	H67C **	H67D **

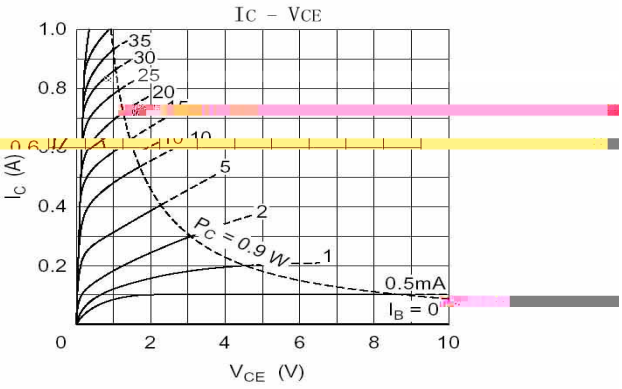
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}		120	V
Collector to Emitter Voltage	V_{CEO}	2SD667T	80	V
		2SD667AT	100	
Emitter to Base Voltage	V_{EBO}		5.0	V
Collector Current (DC)	I_C		1.0	A
Collector Current (Pulse)	I_{CP}		2.0	A
Collector Power Dissipation	P_C		500	mW
Collector Power Dissipation*	$*P_C$		1.0	W
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

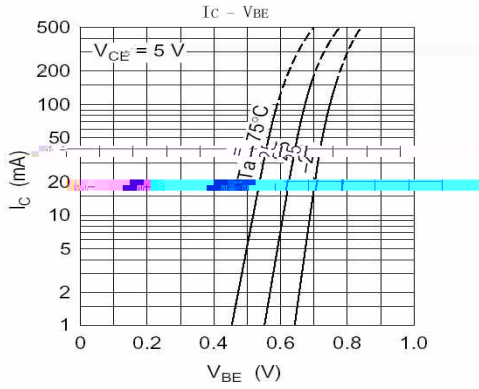
*:mounted on ceramic substrate(250mm^2×0.8t).

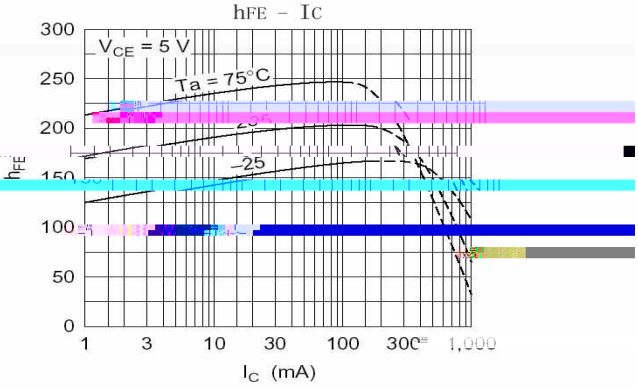
* 250mm

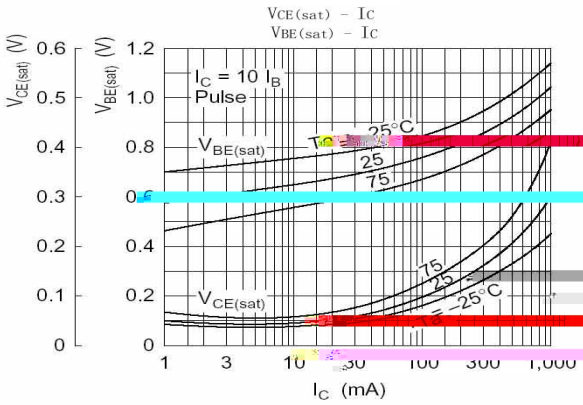
/ Electrical Characteristic Curve

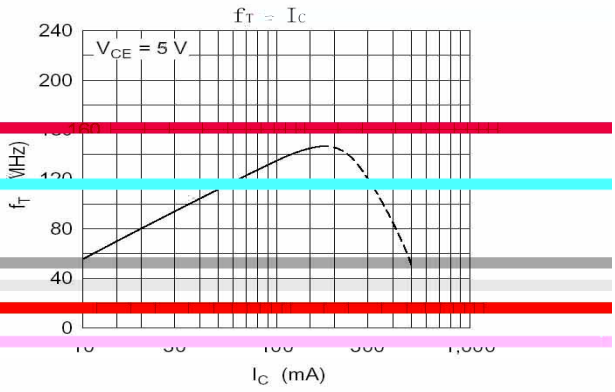




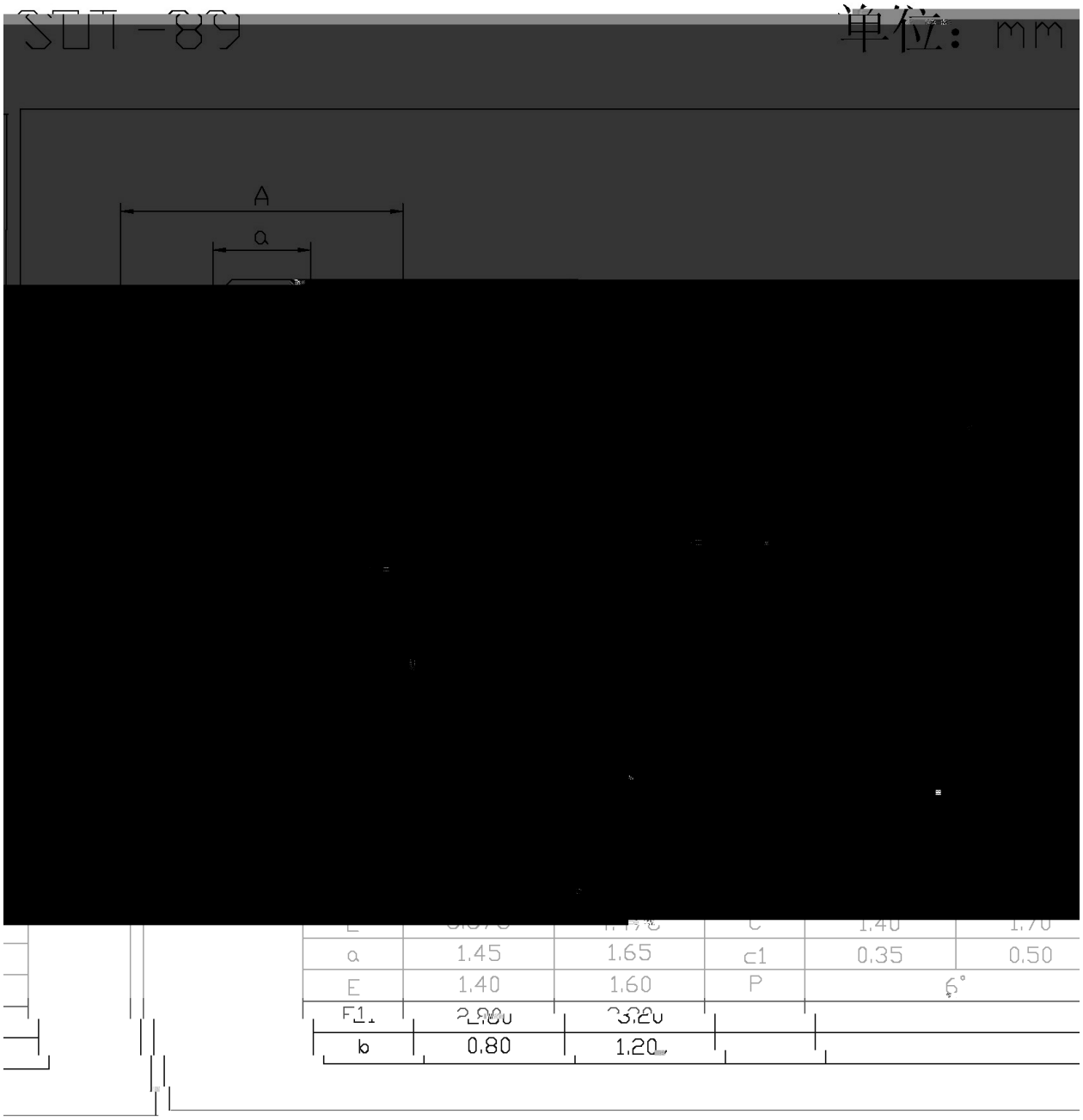




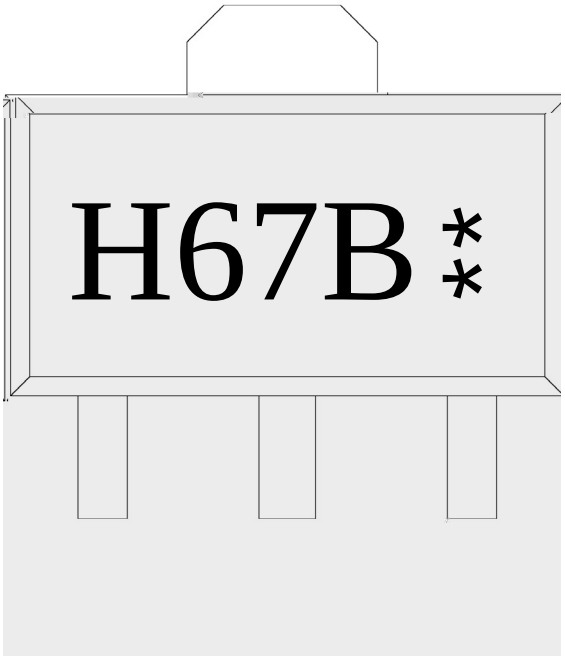




/ Package Dimensions



/ Marking Instructions



H:

67

B: h_{FE}

**

Note:

H:	Company Code.
67:	Product Type.
B:	h_{FE} Classifications Symbol
**:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)